

N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56 3 June 2016

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

Features and benefits 2.

- Advanced TrenchMOS provides low R_{DSon} and low gate charge •
- Logic level gate operation
- Avalanche rated, 100% tested •
- LFPAK provides maximum power density in a Power SO8 package

Applications 3.

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- Synchronous rectifier in LLC topology
- Chargers & adaptors with $V_{out} < 10 V$
- Fast charge & USB-PD applications •
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	167	W
Static char	acteristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	5.4	7.2	mΩ
Dynamic cl	naracteristics	·					
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	12	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFT 4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
PSMN5R6-60YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN5R6-60YL	5R6L60

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	72	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	405	А
T _{stg}	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	405	А
Avalanche i	ruggedness			1		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[2][3]	-	88.2	mJ

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

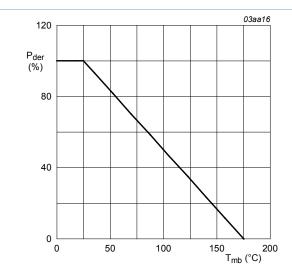
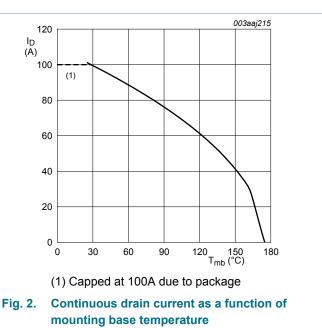


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

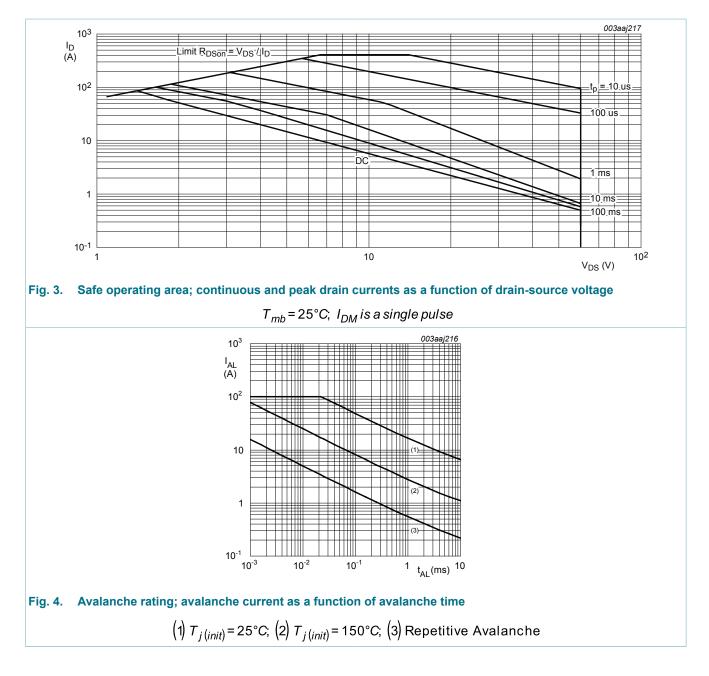


 $V_{GS} \ge 5V$

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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	0.9	K/W

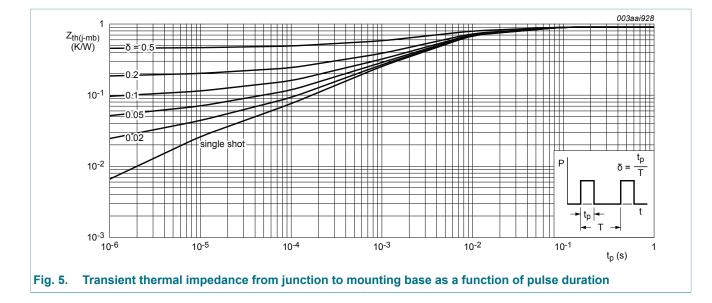
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS} drain-	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> <u>Fig. 10</u>	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	5.4	7.2	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	4.7	5.6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; <u>Fig. 11; Fig. 12</u>	-	-	16.3	mΩ
Dynamic ch	aracteristics	· · ·				
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V;	-	66.8	-	nC
		T _j = 25 °C; <u>Fig. 13; Fig. 14</u>				
		I_D = 25 A; V_{DS} = 48 V; V_{GS} = 5 V;	-	35	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	9.5	-	nC

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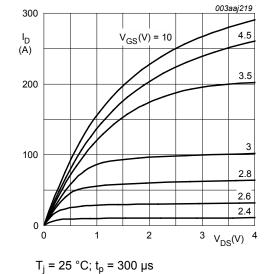
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Symbol	Parameter	Conditions	Mir	тур	Max	Unit
Q _{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	3769	5026	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	341	409	pF
C _{rss}	reverse transfer capacitance		-	185	253	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V;	-	19.3	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	36.4	-	ns
t _{d(off)}	turn-off delay time		-	49.4	-	ns
t _f	fall time		-	32.1	-	ns
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·	I	1		
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.81	1.2	V
+		$L = 20 \text{ A} \cdot dL/dt = 100 \text{ A}/\text{us} \cdot \text{V} = 0 \text{ V}$		22.1		nc

Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	18.1	-	nC
t _{rr}	-		-	23.1	-	ns





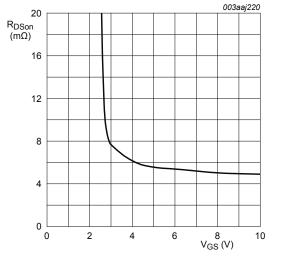


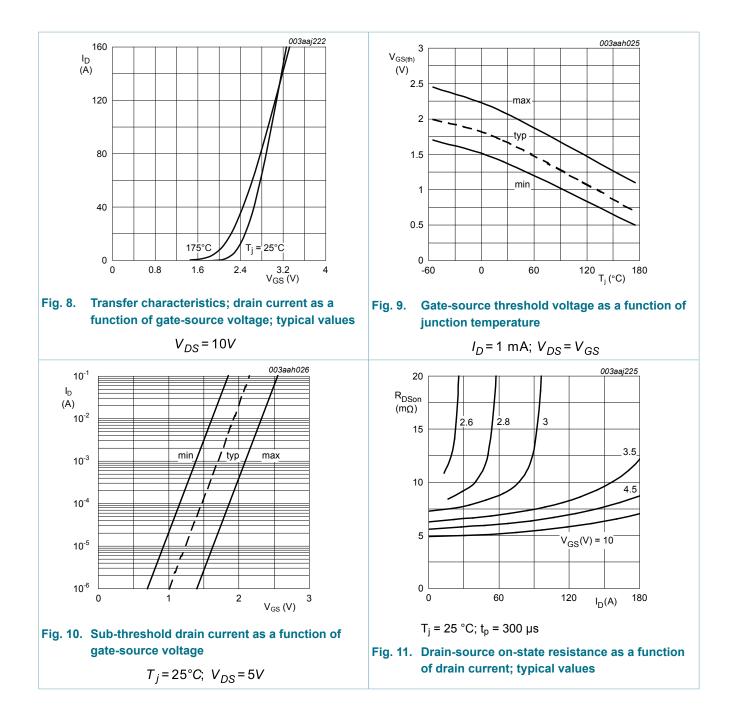
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$

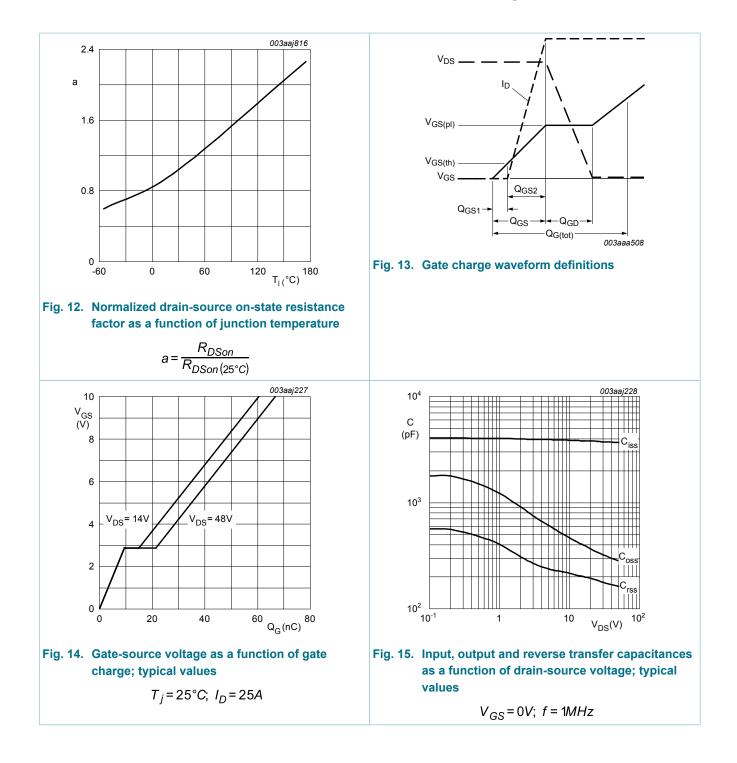
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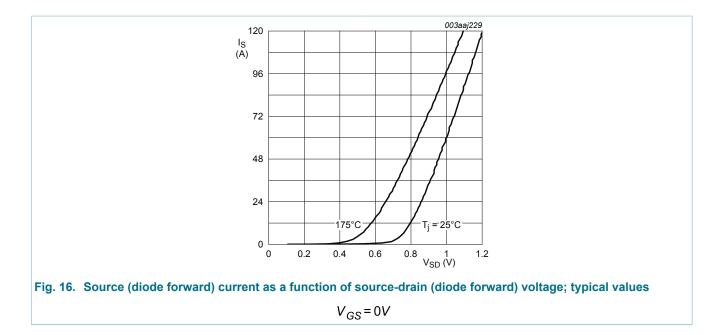


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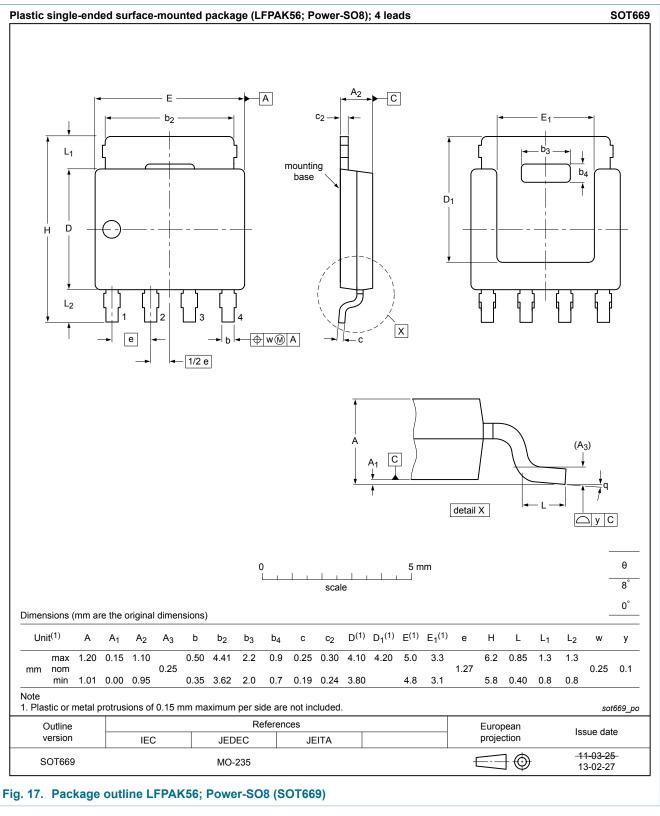
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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